



Sample &

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DRV8808

SLVS857B-DECEMBER 2009-REVISED JANUARY 2015

DRV8808 Combination Motor Driver With DC-DC Converter

1 Features

- Three DC Motor Drivers
 - Up to 2.5-A Current Chopping
 - Low Typical ON Resistance (R_{DSON} = 0.5 Ω at T_J = 25°C)
- Three Integrated DC-DC Converters
 - ON/OFF Selectable Using CSELECT Pin and Serial Interface
 - Outputs Configurable With External Resistor Network From 1 V to 90% of V_M Capability for All Three Channels
 - 1.35-A Output Capability for All Three Channels
- One Integrated LDO Regulator
 - Output Configurable With External Resistor Network from 1 V to 2.5 V
- 550-mA Output Capability
- 7-V to 40-V Operating Range
- Serial Interface for Communications
- Thermally Enhanced Surface-Mount Package 48-Pin HTSSOP With PowerPAD[™] (Eco-Friendly: RoHS and No Sb/Br)
- Power-Down Function (Deep-Sleep Mode)
- Reset Signal Output (Active Low)
- Reset (All Clear) Control Input

2 Applications

- Printers
- Document Scanners
- POS
- Copiers

3 Description

The DRV8808 device provides the integrated motor driver solution for printers. The chip has three full H-bridges and three buck DC-DC converters.

The output driver block for each consists of Nchannel power MOSFETs configured as full Hbridges to drive the motor windings. The device can be configured to use internal or external current sense for winding current control.

The SPI input pins are 3.3-V compatible and have inputs that are 5-V tolerant.

The DRV8808 has three DC-DC switched-mode buck converters to generate a programmable output voltage from 1 V up to 90% of V_M , with up to 1.35-A load current capability.

The device is configured using the CSELECT terminal at start-up, and serial interface during run time.

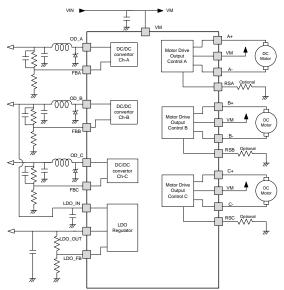
An internal shutdown function is provided for overcurrent protection, short-circuit protection, undervoltage lockout, and thermal shutdown. Also, the device has the reset function at power on, and the input on the nReset pin.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
DRV8808	HTSSOP (48)	12.50 mm x 6.10 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Typical Application Schematic



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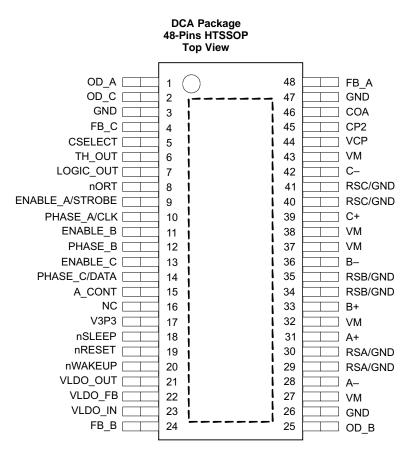
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5 Pin Configuration and Functions



Pin Functions

PIN		1/O	PU/PD	SHUNT	DESCRIPTION	
NAME	NO.	1/0	PU/PD	R	DESCRIPTION	
A-	28	0	_	_	Motor drive output for winding A-	
A+	31	0	_	_	Motor drive output for winding A+	
A_CONT	15	I	Down	100k	DC-DC A converter control (L = Enable)	
B-	36	0	_	_	Motor drive output for winding B-	
B+	33	0	_	_	Motor drive output for winding B+	
C-	42	0	—	—	Motor drive output for winding C-	
C+	39	0	—	—	Motor drive output for winding C+	
CP1	46	0	—	—	Charge pump bucket capacitor output (low side)	
CP2	45	0	_	_	Charge pump bucket capacitor output (high side)	
CSELECT	5	I	Up	200k	DC-DC converter startup selector	
ENA / STB	9	I	Down	100k	Enable input for DC motor A control / SPI STROBE	
ENB	11	I	Down	100k	Enable input for DC motor B control	
ENC	13	I	Down	100k	Enable input for DC motor C control	
FB_A	48	I	_	_	Feedback signal for DC-DC converter A	
FB_B	24	I	_	_	Feedback signal for DC-DC converter B	
FB_C	4	I	_	_	Feedback signal for DC-DC converter C	
GND	3	_	_	_	Ground	
GND	26	_	_	_	Ground	
GND	47	—		—	Ground	

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NSTRUMENTS

FEXAS

Pin Functions (continued)

PIN				SHUNT	DESCRIPTION		
NAME	NO.	I/O	PU/PD	R	DESCRIPTION		
LOGIC_OUT	7	0	—	_	Information monitoring output (open drain)		
NC	16	NC	_	_	Do not connect		
nORT	8	0	_	_	Reset output (open drain)		
nReset	19	I	Up	200k	Reset input (L: reset, H/open: normal operation)		
nSLEEP	18	I	Down	100k	Enable/disable, SPI selector		
nWAKEUP	20	I	Up	200k	Wake-up pin for DeepSleep mode (L = WAKEUP)		
OD_A	1	0	_	_	Output for DC-DC switch mode regulator A		
OD_B	25	0	_	_	Output for DC-DC switch mode regulator B		
OD_C	2	0	_	_	Output for DC-DC switch mode regulator C		
PHA / CLK	10	I	Down	100k	Phase input for DC motor A control / SPI CLOCK		
PHB	12	I	Down	100k	Phase input for DC motor B control		
PHC / DATA	14	I	Down	100k	Phase input for DC motor C control / SPI DATA		
RSA / GND	30	0	_	_	Motor drive current sensing resistor A / GND power		
RSKA / GND	29	I	_	_	Motor drive current sensing resistor A / GND Kelvin		
RSB / GND	35	0	_	_	Motor drive current sensing resistor B / GND power		
RSKB / GND	34	I	—	—	Motor drive current sensing resistor B / GND Kelvin		
RSC / GND	41	0	_	_	Motor drive current sensing resistor C / GND power		
RSKC / GND	40	I	_	_	Motor drive current sensing resistor C / GND Kelvin		
TH_OUT	6	0	_	_	Temperature warning output (open drain)		
V3p3	17	0	_	_	Bypass for internal 3.3-V regulator		
VCP	44	0	—	—	Charge pump output		
VLDO_FB	22	I	_	_	LDO voltage regulator feed back		
VLDO_IN	23	I	_	_	LDO voltage regulator input		
VLDO_OUT	21	0	_	_	LDO voltage regulator output		
VM	27	_	_	_	Voltage supply for motors and regulators		
VM	32	_	_	_	Voltage supply for motors and regulators		
VM	37	_		_	Voltage supply for motors and regulators		
VM	38				Voltage supply for motors and regulators		
VM	43				Voltage supply for motors and regulators		



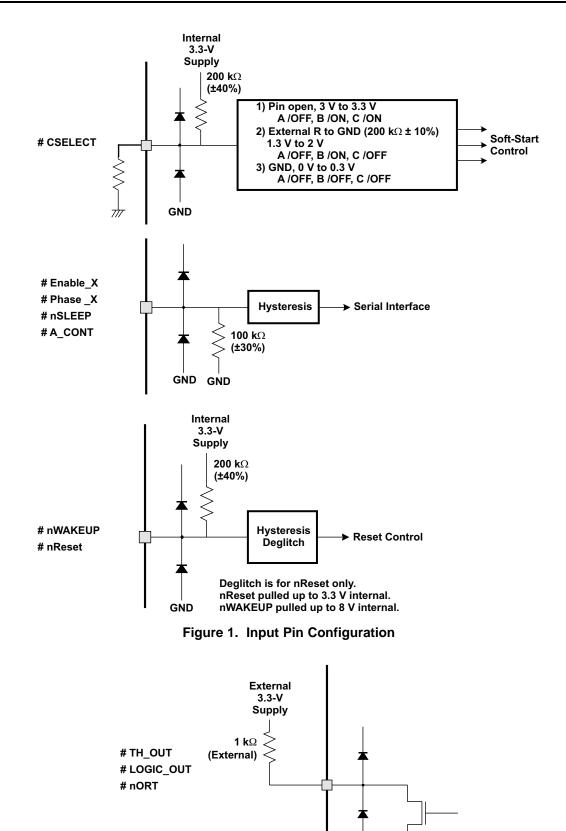


Figure 2. Open-Drain Output Pin Configuration

 $\frac{1}{7}$

GND

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{M}	Supply voltage		40	V
	Logic input voltage, serial I/F, A_CONT, nReset, and so forth (2)	-0.3	5.5	V
	TH_OUT, nORT, LOGIC_OUT, CSELECT	-0.3	3.6	V
	nWAKEUP	-0.3	8	V
	Continuous total power dissipation (in case $\theta_{JA} = 20^{\circ}C/W$)		4	W
	Continuous motor-drive output current for each H-bridge (100 ms)		2.5	А
	Continuous DC-DC converter output current ⁽³⁾		1.35	А
T_J	Operating junction temperature (1 hour)		190	°C
	Lead temperature 1.6 mm (1/16 in) from case for 10 s		260	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The negative spike less than -5 V and narrower than 50-ns width should not cause any problem.

(3) May shut down due to regulator OCP.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 $^{\left(2\right) }$	±500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

	MIN	NOM	MAX	UNIT
Supply voltage range, V_M for motor control	18	27	38	V
Supply voltage range for DC-DC converter (V_M)	7	27	38	V
Operating ambient temperature range	-10		85	°C
Operating junction temperature range	0		135	°C

6.4 Thermal Information

		DRV8808	
	THERMAL METRIC ⁽¹⁾	HTSSOP (DCA)	UNIT
		48 PINS	
$R_{ extsf{ heta}JA}$	Junction-to-ambient thermal resistance	28.1	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	15.6	
$R_{ heta JB}$	Junction-to-board thermal resistance	10.2	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	0.3	C/VV
Ψ_{JB}	Junction-to-board characterization parameter	10.1	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	0.9	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

 $T_J = 0^{\circ}C$ to 135°C, $V_M = 7$ V to 38 V (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY (SL	EEP) CURRENT						
I _{SLEEP1}	Supply (sleep) current 1	nSLEEP = L,	DC-DC all off		3	5.5	mA
I _{SLEEP2}	Supply (sleep) current 2	nSLEEP = L, Regulators enabled	V _M = 8 V, No load		6	8	mA
I _{SLEEP3}	Supply (sleep) current 3	nSLEEP = L, Regulators enabled	V _M = 38 V, No load		6	8	mA
IDEEP_SL	Supply (deep sleep) current ⁽¹⁾	V _M = 38 V			0.7	1	mA
DIGITAL INT	ERFACE CIRCUIT			L.			
V _{IH}	Digital high-level input voltage	Digital inputs		2		3.6	V
IIH	Digital high-level input current	Digital inputs				100	μA
V _{IL}	Digital low-level input voltage	Digital inputs				0.8	V
IIL	Digital low-level input current	Digital inputs				100	μA
V _{hys}	Digital input hysteresis	Digital inputs			0.45		V
T _{deg_nReset}	nReset input deglitch time			2.5		7.5	μs
T _{filt_ACONT}	A_CONT filter time ⁽²⁾			30		70	μs
	JMP VCP (CP = 0.1 μF to 0.47 μF,	Cblk = 0.01 µF ±20%)					
V _O (CP)	Output voltage	$I_{LOAD} = 0 \text{ mA},$	V _M > 15 V	V _M + 10		V _M + 13	V
f(CP)	Switching frequency				1.6		MHz
t _{start}	Start-up time	C _{Storage} = 0.1 µF,	V _M ≥ 15 V		0.5	2	ms
V3P3 OUTP	UT			L.		i	
V _{3p3}	Output voltage ⁽³⁾			3	3.3	3.6	V
C _{bypass}	Output capacitor			0.08	0.1	10	μF
	CLOCK OSCI			L.			
f _{OSCi}	System clock rrequency			5.76	6.4	7.04	MHz
CSELECT F	OR DC-DC STARTUP SELECTION	1		L.			
V _{CS0}	DC-DC all off			0		0.3	V
V _{CS1}	Turn ON ODB	Pull down by external	200-kΩ resistor	1.3		2	V
V _{CS2}	Turn ON ODB then ODC	As pin open		3		3.6	V
	JLATOR ⁽⁴⁾⁽⁵⁾⁽⁶⁾			4		I	
VLDO _{IN}	LDO input voltage			3		3.6	V
VLDO _{FB}	Feedback voltage				1		V
		$1 \text{ V} \leq \text{VLDO}_{\text{OUT}} \leq 1.8$	V		±5%		
VLDO _{OUT}	Output voltage range	1.8 V ≤ VLDO _{OUT} ≤ 2	.5 V		±3%		
I _{OUT}	Load capability					500	mA
I _{OCP}	OCP current				725	1100	mA
t _{Ideg}	OCP deglitch			3	8	13	μs
V _{ovp}	Overvoltage protection	% to nominal Voutx d (VFB increasing)	letected at VFB	25%	30%	35%	
V _{uvp}	Undervoltage protection	% to nominal Voutx d (VFB decreasing)	etected at VFB	-25%	-30%	-35%	

(1) Deep Sleep shuts down majority of the device and runs minimal circuits (internal bias circuits and the nWAKEUP pin). Deep Sleep is entered by writing 1 to Setup Register, Bank 1, Bit 11. Device is restarted by pulling nWAKEUP pin low or power cycling V_M. Deep Sleep functionality only available for $V_M > Vth_{VM+}$.

(2) A_CONT is filtered for both high and low levels.

V3p3 bypass pin is not meant to be used as a supply. (3)

(4) LDO can be bypassed by either load configuration 1 or 2.

Typical values for external components should be chosen such that when the tolerance is added to the typical, the values remain (5) between the maximum and minimum specifications listed.

When LDO is not used, recommend connecting VLDO_IN to GND, VLDO_OUT to GND, and VLDO_FB to FB_B. (6)

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Electrical Characteristics (continued)

	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
t _{Vdeg}	UVP/OVP deglitch time			3	8	13	μs
C _{L1}		Electrolytic load capa	citance	27		120	μF
C _{ESR1}	Load bypass configuration 1	ESR of load capacita	nce	0.05		2	Ω
C _{C1}		Ceramic load capacit	ance	0		0.4	μF
C _{L2}		Electrolytic load capa	citance	80	100	120	μF
C _{ESR2}	Load bypass configuration 2	ESR of load capacitance		0.05		0.2	Ω
C _{C2}		Ceramic load capacitance		0		3	μF
THREE DC-	DC CONVERTER						
$V_{M OPE_X}$	Operating supply voltage range ratio to V _{OUT}	I _O < 0.6 A	$Vth_{VM} < V_M < 7 V$			0.8 x V _M	V
			20 V < V _M < 38 V			0.9 x V _M	
ODx	Regulator output voltage	$20 \text{ V} < \text{V}_{\text{M}} < 40 \text{ V}$	0°C < T _J < 125°C	-3%	Vo	3%	
			125°C < T _J < 135°C	-4%	Vo	4%	
		6.5 V < V _M < 20 V		-5%	Vo	5%	
		V _M = 7 V, V _O = 5.5 V		-5%	Vo	5%	
		$V_{M} = 7 V, V_{O} = 1 V$	0°C < T _J < 125°C	-3%	Vo	3%	
			125℃ < T _J < 135℃	-4%	Vo	4%	
		$Vth_{VM-} < V_M < 6.5 V$, $V_O \le 3.3 V$		-5%	Vo	5%	
FBx	FBx pin voltage				1		V
I _{O ODx}	Output current (DC)	V _M > 15 V	V _M > 15 V			1.35	А
I _{O ODx2}	Output current (DC) at low V_M	V _M = 7 V, V _O = 5.5 V				0.6	А
I _{O ODx3}	Output current (DC) at low V_M	V _M = 7 V, V _O = 3.3 V				1.2	А
R _{DSON} ⁽⁷⁾	FET on-resistance at 0.8 A for	T _J = 70 °C			0.85	1.05	Ω
	OD_x V _M > 15 V	T _J = 135 °C			1	1.2	
L	Inductor	V _{OUT} = 1.0 V					μH
		V _{OUT} ≥ 3.3 V			330		
С	Capacitor	V _{OUT} = 1.0 V	270		330	μF	
		V _{OUT} ≥ 3.3 V			220		
THREE DC-	DC CONVERTER PROTECTION			1			
I _{O DD ODx}	Overcurrent detect for OD_x source	Peak current in each	ON cycle	1.35		2.7	А
t _{ODXdeg}	Cycle by cycle Idetect deglitch			100	200	400	ns
t _{ODXSD}	DC-DC shutdown filter	Number of consecutiv	ve cycles with Idetect		4		chop cycles
V _{ovpx}	Overvoltage protection	% to nominal Voutx of (VFB increasing)	letected at VFB	25%	30%	35%	
V _{uvpx}	Undervoltage protection	% to nominal Voutx detected at VFB (VFB decreasing)		-25%	-30%	-35%	
t _{VXdeg}	UVP/OVP deglitch time			3	8	13	μs
t _{sst}	Start-up time with soft start					56	ms
V _{stover}	Start-up overshoot	Ratio to Vo				3%	
	/ISORY ^{(8) (9)}	·		•		1	
Vth _{VM-}	nORT, for V_M low threshold	V _M decreasing		4.5	5	6	V
Vth _{VM+}	nORT, for V _M high threshold	V _M increasing		5.5	6	6.79	V

(7)

(8)

 R_{DSON} at T = 135°C guaranteed by characterization. Production test will be done at T = 25°C/70°C. V_M must be $V_M > Vth_{VM+}$ to start up internal DC-DC converter. When V_M goes down below Vth_{VM+}, the VUVPx (undervoltage protection in DC-DC) are masked. The DC-DC converter is shut off by (9) nORT assertion at Vth_{VM -}.



Electrical Characteristics (continued)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vth _{VMh}	nORT, for V_M detect hysteresis	$Vth_{VM+} - Vth_{VM-}$	0.5	1		V
Vth _{VM2}	For motor driver off ⁽¹⁰⁾				15	V
t _{VMfilt}	Vth V_M monitor filtering time	For Vth V _M detect	4		30	μs
t _{VM2filt}	Vth V_{M2} monitor filtering time	For Vth V _{M2} detect	30		60	ms
THERMAL S	SHUTDOWN: TSD ⁽¹¹⁾ ⁽¹²⁾	· · · · ·				
T _{TSD}	Thermal shutdown set points		150	170	190	°C
t _{TSDdeg}	TSD deglitch time		30	60	90	μs
	URE WARNING: PRE-TSD ⁽¹³⁾ (12)	+ +			· ·	
PreTSD	Temperature warning	Assert at TH_OUT pin	115	135	155	°C
OPEN-DRA	IN OUTPUTS (NORT, LOGIC_OUT,	TH_OUT)				
V _{OH}	High-state voltage	$RL = 1 k\Omega$ to 3.3 V	3			V
V _{OL} ⁽¹⁴⁾	Low-state voltage	$RL = 1 k\Omega$ to 3.3 V			0.3	V
I _{OL} ⁽¹⁴⁾	Low-state sink current	Vo = 0.25 V	2			mA
t _r ⁽¹⁵⁾	Rise time	10% to 90%			1	μs
t _f ⁽¹⁵⁾	Fall time	90% to 10%			50	ns .
NORT DELA	AY: STARTUP SEQUENCE ⁽¹⁶⁾ ⁽¹⁷⁾				I	
Tord1	nORT delay 1	Reset deassertion from $Vth_{VM+} < V_M$, for DC/DC wake up failing	200	300	390	ms
Tord3	DC-DC turn on delay	From one DC-DC wake up to following DC- DC to go soft-start sequence 5		10	15	ms
Tord4	nORT delay 4	Reset deassertion from 2nd DC-DC wake up	60	120	180	ms
NRESET IN	PUT ⁽¹⁶⁾				1	
Treset	nReset assertion to nORT assertion delay	nReset falling to nORT failing		5	10	μs
H-BRIDGE I	DRIVERS (OUTX+ AND OUTX-) CC	DNDITION: $V_{\rm M} = 15$ V to 38 V ⁽¹⁸⁾				
I _{OUT1(max)}	Peak output current 1	Less than 500-ns period			6.8	А
I _{OUT2(max)}	Peak output current 2	Less than 100-ms period			2.42	А
R _{DSON}	FET ON resistance at 0.8 A	$T_J = 70^{\circ}C$		0.55	0.65	Ω
		T _J = 135°C		0.7	0.85	
I _{CEX}	Output leakage current	VOUTX = 0 V or 10			10	μA
I _{OC Motor}	Motor overcurrent threshold for each H-bridge ⁽¹⁸⁾		3		8	A
Fchop	Motor chopping frequency = FOSCM/8		90	100	110	kHz
DC MOTOR	DRIVERS					
t _r	Rise time	V _M = 35 V 20% to 80%	50		200	ns
t _f	Fall time	V _M = 35 V 20% to 80%	50		200	ns
t _{PDOFF}	Enable or strobe detection to sink or source gate OFF delay		50	150	400	ns

(10) No nORT assertion to Vth_{VM2} detection. (11) TSD does not need thermal hysteresis.

(12) Parametric guaranteed by characterization. Not tested in production.

(13) PreTSD does not need thermal hysteresis.(14) Production test only measures Vol and Iol to ensure timing.

(15) t_r and t_f dominated by external capacitance, pullup resistance, and open-drain NMOS R_{DSON}.
(16) This includes asynchronous timing deviation between the event to the timer clock.

(17) nORT assertion delay is configurable and defined in the serial register section.

(18) When the overcurrent is detected, all the H-bridges are shut down and assert nORT per shutdown configuration.

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Electrical Characteristics (continued)

$T_{.1} = 0^{\circ}C$ to 135°C, $V_{M} =$	7 V	/ to 38 V ((unless otherwise noted)
$1 = 0 = 0 = 100 = 0, v_{\rm M} =$	· / V		

	PARAMETER	TEST CONDITIONS	MIN			UNIT
t _{COD}	Crossover delay time to prevent shoot through		100 ⁽¹⁹⁾	600	1000	ns
t _{PDON}	Enable or strobe detection to sink or source gate ON delay			750		ns
t _{ldeg}	MISD BLANK	[00] ⁽²⁰⁾	1.80	2.25	2.95	
		[01] ⁽²¹⁾	1.20	1.50	2.30	
		[10] ⁽²²⁾	2.35	3.00	3.65	μs
		[11] ⁽²³⁾	2.95	3.75	4.30	
T _{blank}	TBLANK	[00] ⁽²⁴⁾	3.05	3.45	5.50	
		[01] ⁽²⁵⁾	1.90	2.20	4.15	
		[10] ⁽²⁶⁾	4.15	4.70	6.75	μs
		[11] ⁽²⁷⁾	5.30	5.95	8.25	
VRS _{TRIP}	Internal current trip	00	1.18	1.4	1.62	
		01	1.48	1.7	1.92	^
		10	1.68	1.9	2.12	
		11	1.98	2.2	2.42	
	External resistor sense voltage	00	165	185	205	205 230 mV
	trip threshold	01	190	210	230	
		10	240	260	280	mv
		11	290	310	330	
P _{minp}	Minimum pulse width (phase)	(19)			1	μs
P _{mine}	Minimum pulse width (enable)	(19)			1	μs
	ERFACE ⁽²⁸⁾					
f(CLK)	Clock frequency				25	MHz
t _{wh} (CLK)	Minimum high-level pulse width		10			ns
t _{wl} (CLK)	Minimum low-level pulse width		10			ns
t _{dcs}	Setup time, DATA to CLK↓		10			ns
t _{dch}	Hold time, CLK↓ to DATA		10			ns
t _{dss}	Setup time, DATA to STROBE↑		10			ns
t _{dsh}	Hold time, STROBE↑ to DATA		10			ns
css	Setup time, CLK↓ to STROBE↑		20 ⁽²⁹⁾			ns
csh	Hold time, STROBE \uparrow to CLK \downarrow		20 ⁽²⁹⁾			ns
t _{nss}	Setup time, nSLEEP↓ to STROBE↑		4 ⁽³⁰⁾			μs
t _{nsh}	Hold time, STROBE↑ to nSLEEP↑		10			ns
t _w (STRB)	Minimum strobe pulse width		20			ns

(19) t_{COD} , P_{minp} , and P_{mine} not production tested. (20) 3 to 4 periods Fosc/4 + 1 Fosc

(21) 2 to 3 periods Fosc/4 + 1 Fosc

(22) 4 to 5 periods Fosc/4 + 1 Fosc

(23) 5 to 6 periods Fosc/4 + 1 Fosc

(24) 3 Fosc/8 (can add up to 1 additional Fosc/8 + 1.5 Fosc at phase or enable change due to asynchronous ambiguity)

(25) 2 Fosc/8 (can add up to 1 additional Fosc/8 + 1.5 Fosc at phase or enable change due to asynchronous ambiguity)

(26) 4 Fosc/8 (can add up to 1 additional Fosc/8 + 1.5 Fosc at phase or enable change due to asynchronous ambiguity)

(27) 5 Fosc/8 (can add up to 1 additional Fosc/8 + 1.5 Fosc at phase or enable change due to asynchronous ambiguity)

(28) Serial interface timing will not be tested parametrically in production.
(29) DATA value at STROBE is address bit for Setup and Extended Setup register so setup and hold times apply to DATA relative to STROBE. CLK and DATA also require setup and hold times relative to each other. Therefore, CLK and STROBE setup and hold timing is the summation of both.

(30) Internal filter on nSLEEP to STROBE drives this specification.



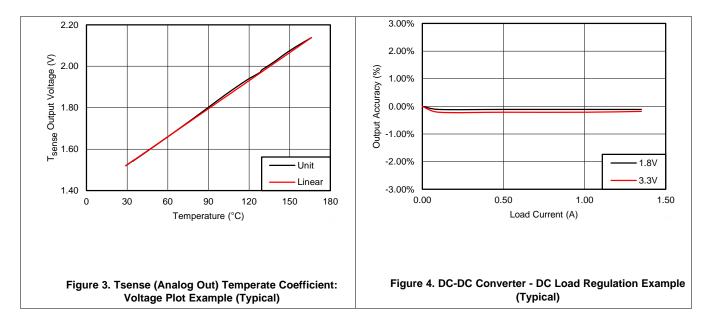
Electrical Characteristics (continued)

Т. –	0°C to	135°C	$V_{\rm ell} = 7 V$	to 38 V	lunlass	otherwise noted)	
1.1=		133 0,	$v_{\rm M} = i v$	10 30 V	(11111111111111111111111111111111111111	otherwise noted)	

· · · · · · · · · · · · · · · · · · ·							
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
SERIAL INTERFACE: ID MONITOR FUNCTION AT LOGIC_OUT PIN, EXTENDED SETUP MODE ⁽³¹⁾							
t _{ODL}	0 data output delay bit 3 to 0 (ext-setup) = (1100)	From strobe rise to Logic_out (1 k Ω to external 3.3 V)			4000	ns	
t _{ODH}	1 data output delay bit 3 to 0 (ext-setup) = (1111)				4000	ns	

(31) Serial interface timing will not be tested parametrically in production.

6.6 Typical Characteristics





7 Detailed Description

7.1 Overview

The Combo Motor Driver provides the integrated motor driver solution for printers and other applications. The chip has three full H-bridges and three Buck DC-DC converters, and one LDO.

The output driver block for each consists of N-channel power MOSFET's configured as full H-bridges to drive the motor windings. Device can be configured to utilize internal or external current sense for winding current control.

The SPI input pins are 3.3-V compatible and 5-V tolerant inputs.

The Combo Motor Driver has three, DC-DC switch mode buck converters to generate a programmable output voltage.

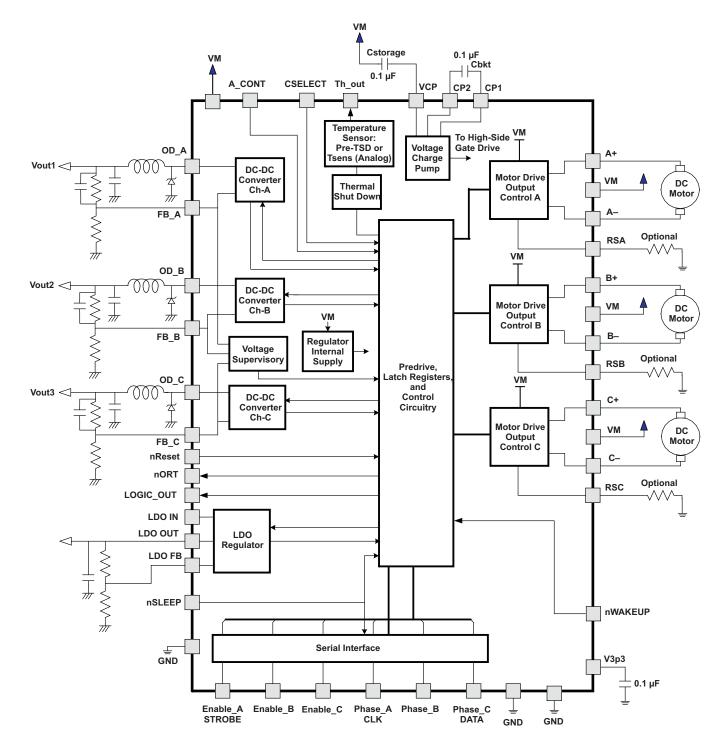
The device is configured using the CSELECT terminal at start up, and serial interface during run time.

An internal shutdown function is provided for over current protection, short circuit protection, under voltage lockout and thermal shutdown.

The device also has the reset function at power on, and the input on nReset pin.



7.2 Functional Block Diagram





7.3 Feature Description

7.3.1 Setup Mode, Extended Setup Mode, Power-Down Mode

The motor output mode is configured through the SIP (DATA, CLK and STROBE) when nSLEEP = L. After set up, the nSLEEP pin must be pulled high for normal motor drive control. The value on the DATA line at the positive edge of STROBE when nSLEEP is low, selects whether the data is written to the Setup or Extended Setup registers. Setup is selected for DATA = L; Extended Setup is selected for DATA = H.

The condition, which the device requires for set up (initialize), is after the nORT (Reset) output goes H level from L level (power on, recovery from $V_M < 7$ V). During nSLEEP in L level, all the motor-drive functions are shut down and their outputs are high-impedance state. This device forces motor-driver functions to shut down for the power-down mode, and is not damaged even if nSLEEP is asserted during motor driving.

Data is shifted at all times, regardless of nSLEEP. Care must be taken to ensure valid data has been shifted into the internal shift register, before the STROBE rising edge, occurs while nSLEEP is LO.

7.3.1.1 Operation Setup Register Bit Assignment

BANK	BIT	FUNCTION	DEFAULT	COMMENT
	0	Tblank A 0	0	00: 3.75 μs, 01: 2.50 μs
	1	Tblank A 1	0	10: 5.00 µs, 11: 6.25 µs
	2	Tblank B 0	0	00: 3.75 μs, 01: 2.50 μs
	3	Tblank B 1	0	10: 5.00 µs, 11: 6.25 µs
	4	Tblank C 0	0	00: 3.75 μs, 01: 2.50 μs
	5	Tblank C 1	0	10: 5.00 µs, 11: 6.25 µs
	6	DC-DC A Minoff Time	0	0: 2.2 µs, 1: 6.6 µs
0	7	DC-DC A SW	1	
0	8	DC-DC B SW	CSELECT	0: On 1: Off
	9	DC-DC C SW	CSELECT	1. 01
	10	MOTOR CHOPPING 0	0	00: 100 kHz, 01: 50 kHz
	11	MOTOR CHOPPING 1	0	10: 133 kHz, 11: 200 kHz
	12	RESET DELAY CONTROL	0	0: Disable, 1: Enable
	13	LDO ENABLE	Note 1	0: On, 1: Off
	14	DC-DC B Minoff Time	0	0: 2.2 µs, 1: 6.6 µs
	15	Bank Change	0	0: Bank0, 1: Bank1

Table 1. Setup Registers (1) (2) (3)

(1) The LDO default follows the DC/DC B default value based on CSELECT.

- (2) All bits go to default for VM < Vth_{VM}, nReset = L.
- (3) RESET DELAY CONTROL set to 1 delays nORT assertion by 100 us typical. Range is 85 us to 125 us.



Feature Description (continued)

BANK	BIT	FUNCTION	DEFAULT	COMMENT
	0	MISD BLANK AB 0	0	00: 2.25 μs, 01: 1.50 μs
	1	MISD BLANK AB 1	0	10: 3.00 μs, 11: 3.75 μs
	2	MISD BLANK C 0	0	00: 2.25 μs, 01: 1.50 μs
	3	MISD BLANK C 1	0	10: 3.00 µs, 11: 3.75 µs
	4	VRS A	0	0: Disable, 1: Enable
	5	VRS A Level 0	0	VRSA = 0: 00: 1.4 A, 01: 1.7 A 10: 1.9 A, 11: 2.2 A
	6	VRS A Level 1	0	VRSA = 1: 00: 185 mV, 01: 210 mV 10: 260 mV, 11: 310 mV
	7	DC-DC C Minoff Time	0	0: 2.2 µs, 1: 6.6 µs
	8	VRS B	0	0: Disable, 1: Enable
1	9	VRS B Level 0	0	VRSB = 0: 00: 1.4 A, 01: 1.7 A 10: 1.9 A, 11: 2.2 A
	10	VRS B Level 1	0	VRSB = 1: 00: 185 mV, 01: 210 mV 10: 260 mV, 11: 310 mV
	11	DEEP SLEEP	0	0: Disable, 1: Enable
	12	VRS C	0	0: Disable, 1: Enable
	13 VRS C Level 0	0	VRSC = 0: 00: 1.4 A, 01: 1.7 A 10: 1.9 A, 11: 2.2 A	
	14	VRS C Level 1	0	VRSC = 1: 00: 185 mV, 01: 210 mV 10: 260 mV, 11: 310 mV
	15	Bank Change	0	0: Bank0, 1: Bank1

Table 1. Setup Registers ^{(1) (2) (3)} (continued)

BANK	BIT	FUNCTION	DEFAULT	COMMENT
NA 0		Signal Select 0	0	See Logic_Out Table
	1	Signal Select 1	0	
	2	Signal Select 2	0	
	3	Signal Select 3	0	
	4	DCDC/LDO ISD Mask	0	0: Disable, 1: Enable
5 DCDC/LDO VSD Mask		0	0: Disable, 1: Enable	
	6	Motor ISD Mask 0		0: Disable, 1: Enable
	7 TSD Mask		0	0: Disable, 1: Enable
	8	Reset Mask C	0	0: Disable, 1: Enable
	9	Reset Mask B	0	0: Disable, 1: Enable
	10	Reset Mask A	0	0: Disable, 1: Enable
	11	Reset Mask SR	0	0: Disable, 1: Enable
	12	Pre TSD	0	0: TSD-20C, 1: Analog output
	13	TSD Cont0	0	See TSD Control Table
	14	TSD Cont1	0	
	15	MISD Cont	0	See MISD Control Table

7.3.1.2 Operation Extended Setup Register Bit Assignment

All bits go to default for V_M < Vth_{VM-}, nReset = L.
 Bits [11:8] are selective shutdown bits. Setting to a 1 makes faults on the associated regulator only shutdown that regulator and allows restart on an nSLEEP L > H transition. Setting to 0 shuts everything down and restarts only for V_M < Vth_{VM-} or nReset = L.

TSD CONT1	TSD CONT0	DC-DC	MOTORS	NORT	LDO	RELEASED BY
0	0	OFF	OFF	LOW	OFF	$V_M < Vth_{VM-}$ or nReset = L
0	1	ON	OFF	HIGH	ON	$V_M < Vth_{VM-}$ or nReset = L or nSLEEP L > H transition
1	0	ON	OFF	PULSE	ON	$V_M < Vth_{VM-}$ or nReset = L or nSLEEP L > H transition
1	1	OFF	OFF	LOW	OFF	V _M < Vth _{VM} or nReset = L

MISD CONT	DC-DC	MOTORS	NORT	LDO	RELEASED BY
0	ON	OFF	PULSE ⁽¹⁾	ON	$V_M < Vth_{VM-}$ or nReset = L or nSLEEP L > H transition
1	OFF	OFF	LOW	OFF	$V_M < Vth_{VM-}$ or nReset = L

(1) PULSE in Control Tables is 40-ms duration.



Table	5.	Logic_	Out
Table	υ.	LUGIU_	Jui

SIGNAL SELECT	FUNCTION (LOGIC_OUT OUTPUT)			
0000	Detect OCP/UVP/OVP on A, output L			
0001	Detect OCP/UVP/OVP on B, output L			
0010	Detect OCP/UVP/OVP on C, output L			
0011	Detect OCP on DC-DC/LDO regulator, output L			
0100	Detect UVP, output L			
0101	Detect OVP, output L			
0110	Detect OCP on motor, output L			
0111	Detect TSD, output L			
1000	Revision code bit 0			
1001	Revision code bit 1			
1010	Revision code bit 2			
1011	Device code bit 0			
1100	Device code bit 1			
1101	N/A			
1110	Detect OCP/UVP/OVP on LDO regulator, output L			
1111	Fix, output H			

7.3.1.3 Deep Sleep Mode

Deep sleep mode can be entered by setting the deep sleep bit (bit 11) on the Setup register to HI. Once deep sleep mode is entered, every single subsystem is disabled, except the block necessary to regain power by making the nWAKEUP input pin LO.

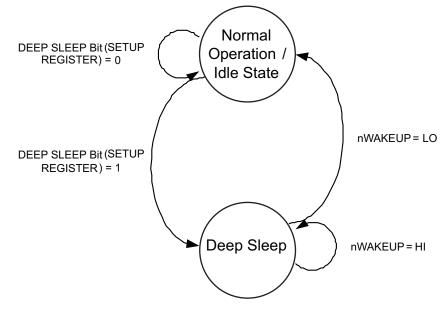


Figure 5. Deep Sleep Mode

7.3.1.4 DC Motor Drive

H-bridges A, B, and C can be controlled by using the ENABLE_X and PHASE_X control lines.

The H-bridge driver operation is available for $V_M > 15$ V.

Internal current sense functionality is present by default. External sensing can be enabled through the serial interface. If enabled, the sense resistor must be placed externally.



NOTE

A capacitor, not larger than 2200 pF, can be placed between each H-bridge output to GND for EMI suppression purposes. It will increase the peak current but will have no impact on the operation.

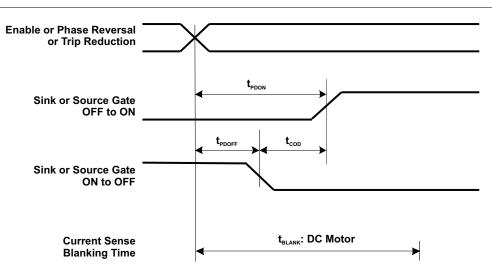


Figure 6. Crossover and Blanking Timing for H-Bridge

The dc motor H-bridges include a t_{BLANK} period to ignore huge current spike due to rush current to varistor capacitance.

7.3.1.5 Short/Open for Motor Outputs

When a short/open situation happens, the protection circuit prevents device damage under certain conditions (short at start-up, etc).

Shutdown is released based on MISD Control in the Extended Setup register.

FAULT CONDITION	NSLEEP	ENABLEX	PHASEX	+ HIGH SIDE	+ LOW SIDE	– HIGH SIDE	- LOW SIDE
0	0	Х	Х	OFF	OFF	OFF	OFF
0	1	0	Х	OFF	OFF	OFF	OFF
0	1	1	0	OFF	ON	ON	OFF
0	1	1	1	ON	OFF	OFF	ON
Motor OCP	Х	Х	Х	OFF	OFF	OFF	OFF
TSD	Х	Х	Х	OFF	OFF	OFF	OFF

Table 6. DC Motor-Drive Truth Table ⁽¹⁾

(1) X = Don't care

7.3.1.6 Charge Pump

The charge-pump voltage generator circuit utilizes, external storage, and bucket capacitors. It provides the necessary voltage to drive the high-side switches, for both DC-DC regulators and motor driver. The charge-pump circuit is driven at a frequency of 1.6 MHz (nom). Recommended bucket capacitance (connected from CP1 to CP2) is 10 nF, rated at 55 V (minimum), and storage capacitance is 0.1 μ F, at 16 V (minimum). The charge-pump storage capacitor, Cstorage, should be connected from the CP output to V_M.

For power save in sleep mode, the charge pump is stopped when $N_SLEEP = L$ and all three regulators are turned OFF. When the part is powered up, the charge pump is started first after the CSELECT capture and, 10 ms later from the CP startup, the first regulator is started up.



Table 7. Charge Pump (1) (2)

FAULT CONDITION	DC-DC CH-A	DC-DC CH-B	DC-DC CH-C	NSLEEP	CHARGE PUMP
Х	OFF	OFF	OFF	0	OFF
Х	ON	Х	Х	Х	ON
Х	Х	ON	Х	Х	ON
Х	Х	Х	ON	Х	ON
0	Х	Х	Х	1	ON
Motor OCP	Х	Х	Х	1	ON
TSD	OFF	OFF	OFF	х	OFF

(1) X = Don't care

(2) DC=DC status in fault condition is determined by serial register settings, TSD Control table, and MISD Control table. These tables define status of charge pump.

7.3.1.7 DC-DC Converters

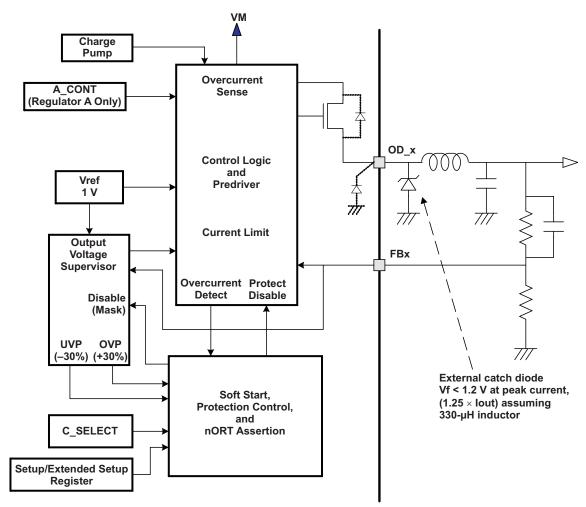


Figure 7. DC-DC Converter

This is a switch-mode regulator with integrated switches, to provide a programmed output set by the feedback terminal. The DC-DC converter has a variable duty cycle topology. External filtering (inductor and capacitor) and external catch diode are required. The output voltage is short circuit protected.

The regulator has a soft-start function to limit the rush current during start-up. It is achieved by using VFB ramp during soft start.

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For unused DC-DC converter channels, the external components can be removed if the channel is set to inactive by the CSELECT pin and register bits. Recommend connecting unused FB pin to GND or V3p3 (pin 17).

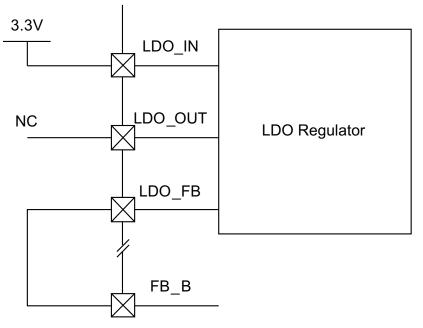


Figure 8. Unused LDO Recommended Connections

For proper termination, it is recommended that, if left unused, the LDO terminals be connected in the following fashion:

- 1. LDO IN must be powered by an input voltage greater than 1 V.
- 2. LDO OUT must be left disconnected.

LDO Feed Back must be connected to the DC/DC Converter Channel B Feed Back terminal.

Table 8. CSELECT for Start-Up (1) (2) (3)

CSELECT	PIN VOLTAGE	DCDC_A	DCDC_B	DCDC_C
Gnd	0 V to 0.3 V	OFF	OFF	OFF
Pull down (by external 200 kΩ)	1.3 V to 2.0 V	OFF	ON	OFF
OPEN	3.0 V to 3.3 V	OFF	ON	ON

(1) The CSELECT pin is connected to internal 3.3-V supply through 200-k Ω resister.

(2) This CSELECT pin control is valid after the PowerON Reset is initiated. Once the Setup Register is set, the DC-DC control follows the bits 7 to 9 on the Setup Register, bank 0, until the next PowerON Reset event occurred.

(3) For OPEN case, B starts up 1st and C follows after 10-ms delay.

Table 9.	Regulator	A Control
----------	-----------	-----------

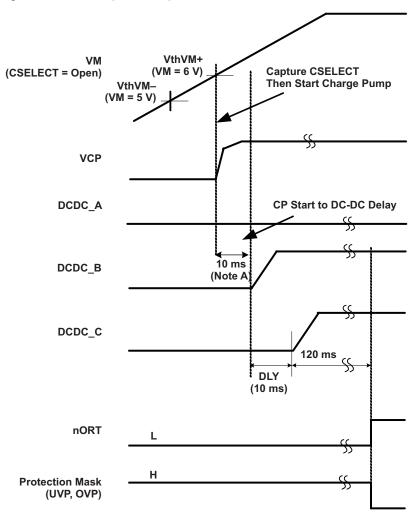
SETUP REGISTER BANK 0, BIT 7	A_CONT	DCDC_A
0	0	ON
0	1	OFF
1	0	OFF
1	1	OFF

7.3.1.8 nReset: Input for System Reset

nReset pin assertion stops all the DC-DC converters and H-bridges. It also resets all the register contents to default values. After deassertion of input, device follows the initial start-up sequence. The CSELECT state is captured after the nReset deassertion (L > H).



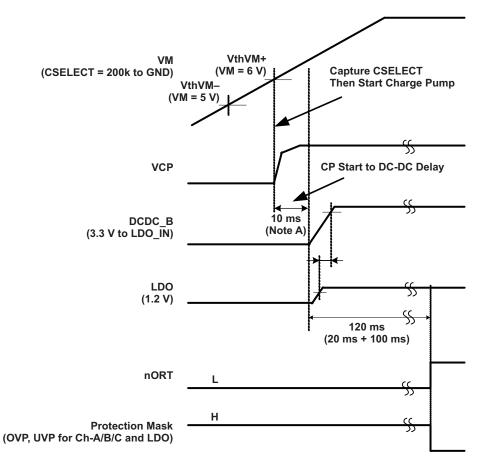
The input is pulled up to internal 3.3 V by a 200-k Ω resistor. When the pin is H or left open, the reset function is released. Also it has deglitch filter of 2.5 µs to 7.5 µs.



- A. Charge-pump wakeup delay, from 10 ms to 20 ms due to asynchronous event capture.
- B. When V_M crosses the Vth_{VM+} (about 6.0 V), the CSELECT state is captured. In case of the CSELECT being open (pulled up to internal 3.3 V), DC-DC regulator channels B and C are turned on.
- C. LDO OCP is masked during protection M\mask time.
- D. In order to avoid false SPI data latching caused by a rising edge on the STB signal, nSLEEP will remain high during the power up stage (VM rising) and until nORT is released.
- E. DC/DC Channel A follows the Regulator A Control table. During power up, DC/DC Channel A starts up disabled (SETUP BANK 0 [7] = 1).

Figure 9. Power-Up Timing (Power-Up With DC-DC Turnon by CSELECT)





- A. Charge-pump wakeup delay, from 10 ms to 20 ms due to asynchronous event capture.
- B. LDO Enable follows DC/DC B Enable during power up and can be controlled using the SETUP register after power up.

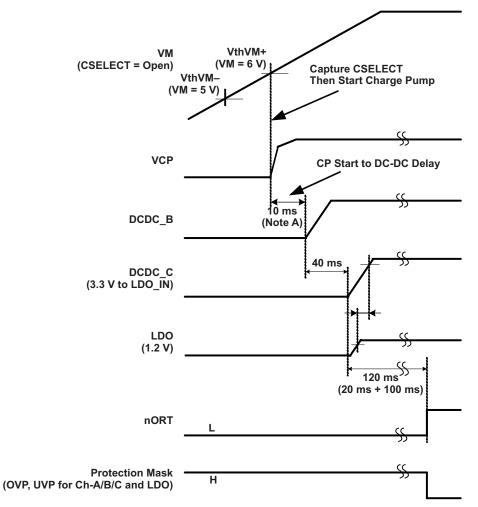
Figure 10. Power-Up Timing (Power-Up With LDO, Supplied by DCDC_B)





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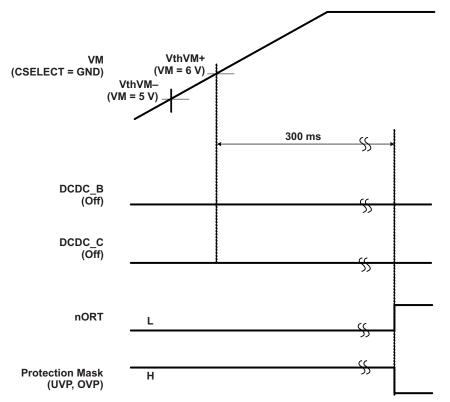
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- A. Charge-pump wakeup delay, from 10 ms to 20 ms due to asynchronous event capture.
- B. LDO Enable follows DC/DC B Enable during power up and can be controlled using the SETUP register after power up. In this case, since LDO_IN is driven by DC/DC Channel C, LDO_OUT will follow DC/DC Channel C.

Figure 11. Power-Up Timing (Power-Up With LDO, Supplied by DCDC_C)

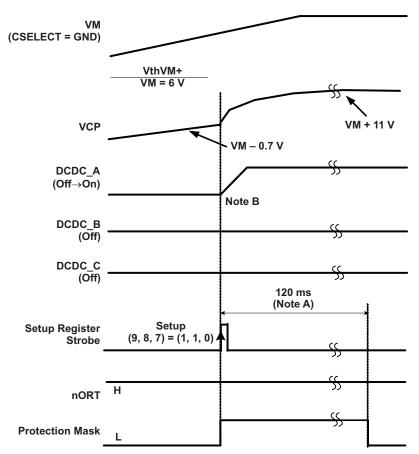




- A. When V_M crosses the Vth_{VM+} (about 6 V) with CSELECT = GND, none of three regulators are turned ON. The nORT output is released to H after 300 ms from Vth_{VM+} crossing.
- B. LDO OCP is masked during protection mask time.

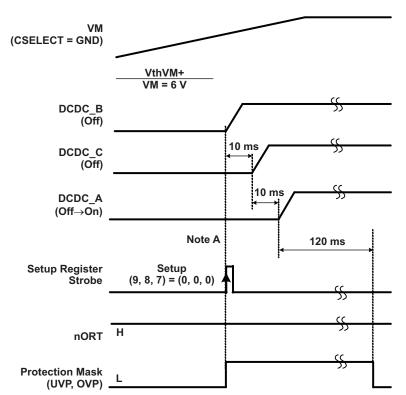
Figure 12. Power-Up Timing (Power-Up Without DC-DC Turnon, CSELECT = GND)





- A. The regulator is started from the strobe input, same as the charge pump. No 10-ms waiting, because the VCP pin already reached to $V_M 0.7$ V.
- B. LDO OCP is masked during protection mask time.
- C. A_CONT must be LOW or OPEN for regulator A to turn on.

Figure 13. Power-Up Timing (DC-DC Regulator Wakeup by Setup Register)



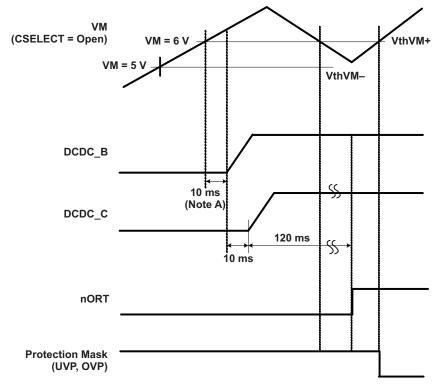
- A. A_CONT must be LOW or OPEN for regulator A to turn on.
- B. LDO OCP is masked during protection mask time.

Figure 14. Power-Up Timing (DC-DC Regulator Wakeup by Setup Register, All Three Channels ON)



7.3.1.9 V_M Start-up/Power-Down and Glitch Condition

1. Start up with V_M glitch (not below Vth_{VM})



A. LDO OCP is masked during protection mask time.

Figure 15. Power-Up Timing With VM Glitch Condition (Not Below Vth_VM-)

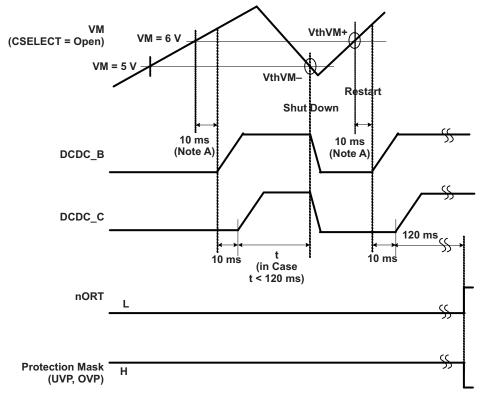


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2. Start up with V_M glitch (below Vth_{VM})

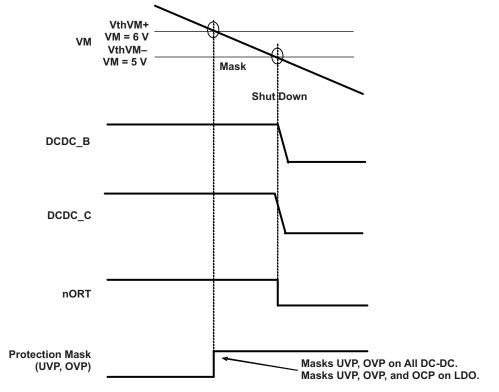


A. LDO OCP is masked during protection mask time.

Figure 16. Power-Up Timing With VM Glitch Condition (Below Vth_VM-)

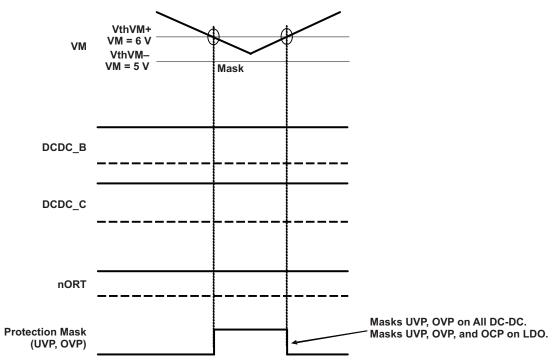


3. Power down (normal)





4. Power down (glitch on V_M)





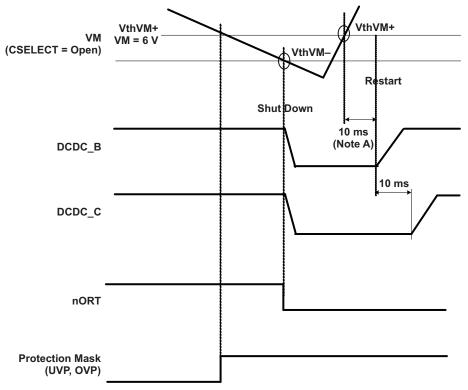


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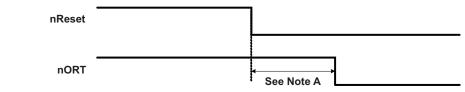
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5. Power down (glitch on V_M below Vth_{VM})



A. LDO OCP is masked during protection mask time.





A. 2.5 μs < (nReset Deglitch + Output Delay) < 10 μs

Figure 20. Shut Down by nReset

7.3.2 Blanking Time Insertion Timing for DC Motor Driving

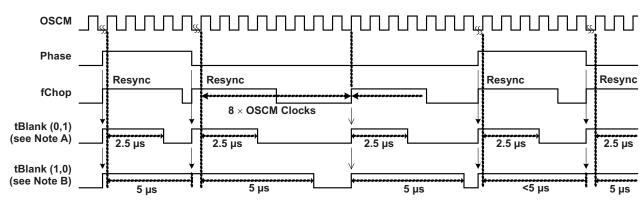
For the dc motor-driving H-bridge, tBlank is inserted at each phase reversal and following each chopping cycle (once in every eight OSCM clocks).

For a large n number (5 or 6), tBlank setup may decrease the Itrip detect window. Care must be taken when optimizing this in the system.

Case A: Phase duty = 25%

- A*1 for setup bit = (1,0)
- A*2 for setup bit = (0,1)



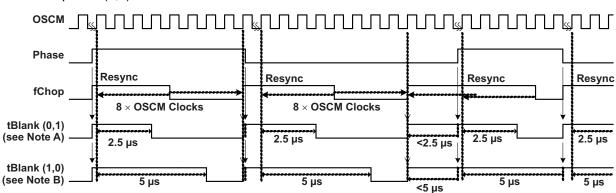


- A. Setup register bit <1:0> = (1,0), tBlank = 5 μ s (or bits <3:2>/<5:4> for H-bridge B/C channel)
- B. Setup register bit <1:0> = (0,1), tBlank = 2.5 µs (or bits <3:2>/<5:4> for H-bridge B/C channel)

Figure 21. Timing for Case A

Case B: Phase duty = 40%

- B*1 for setup bit = (1,0)
- B*2 for setup bit = (0,1)



A. Setup register bit <1:0> = (1,0), tBlank = 5 µs (or bits <3:2>/<5:4> for H-bridge B/C channel)

B. Setup register bit <1:0> = (0,1), tBlank = 2.5 µs (or bits <3:2>/<5:4> for H-bridge B/C channel)

Figure 22. Timing for Case B

7.3.3 Function Table in nORT, Power Down, V_M Conditions

The following is valid only when the protection control bits (in Extended Setup register) are all 0.

Table 10. Block Conditions by Device Status

DEVICE STATUS	CHARGE PUMP	OSCM	nORT	MODE SETTING
nSleep	Active	Active	Inactive	Available
nORT	Inactive	Active	Active	Depend on power down
$V_M < 6 V$ during power down	Active	Active	See timing chart	Depend on power down
4.5 V < V _M	Inactive	Inactive	Active	Unavailable

Table 11. Shutdown Functions

FAULT CONDITION	DCDC_A	DCDC_B	DCDC_C	MOTOR	nORT
DCDC_A UVP/OVP/OCP	Shut down	Shut down	Shut down	Shut down	Asserted (low)
DCDC_B UVP/OVP/OCP	Shut down	Shut down	Shut down	Shut down	Asserted (low)
DCDC_C UVP/OVP/OCP	Shut down	Shut down	Shut down	Shut down	Asserted (low)

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Table 11. Shutdown Functions (continued)

FAULT CONDITION	DCDC_A	DCDC_B	DCDC_C	MOTOR	nORT
Motor OCP	See MISD Control				
	Table	Table	Table	Table	Table
TSD	See TSD Control				
	Table	Table	Table	Table	Table

- Table is valid when the Protection and Reset Mask bits in the Extended Setup register are all 0.
- If Reset Mask (selective shutdown) bits are set, shutdown and release description is in the note following the Extended Setup register definition.
- DC-DC regulators are released at $V_M > Vth_{VM+}$ when V_M increasing. When V_M decreasing, regulators are shut down when $V_M < Vth_{VM-}$. When $Vth_{VM+} > V_M > Vth_{VM-}$, OVP and UVP are masked.
- Motor OCP shutdown release is specified in MISD Control Table.
- TSD shutdown release is specified in TSD Control Table.

7.4 Device Functional Modes

7.4.1 Operation With 7 V < VM < 18 V

The devices starts operating with input voltages above 6.0 V typical. Between 7 V and 18 V, DC-DC converters can operate. Enabling motors in not allowed.

7.4.2 Operation With 18 V \leq VM \leq 38 V

The device can operate with full function. Both DC-DC converter and Motor Drivers can be enabled.

7.5 Programming

7.5.1 Serial Interface

The device has a serial interface port (SIP) circuit block to control DC motor H-bridges, DC-DC regulators, and other functions, such as blanking time, OFF time, and so forth. Because the SIP shares its three lines with three of the motor control signals, the SIP is only available when nSLEEP is low.

nSLEEP	PIN 9	PIN 10	PIN 14	SIP FUNCTIONALITY
L	STB	CLK	DATA	Yes
Н	ENA	PHA	PHC	No

Table 12. Serial Interface

Sixteen-bit serial data is shifted least significant bit (LSB) first into the serial data input (DATA) shift register on the falling edge of the serial clock (CLK). After 16-bit data transfer, the strobe signal (Strobe) rising edge latches all the shifted data. During the data transferring, Strobe voltage level is ok with L level or H level.

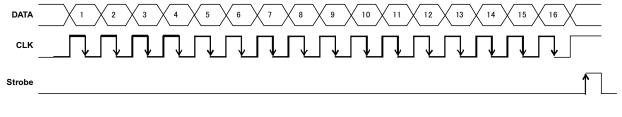


Figure 23. Serial Interface

NOTE

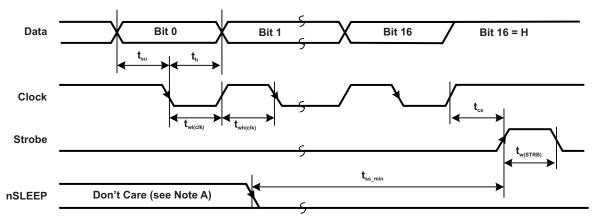
During startup (VM rising), nSLEEP input is set HI, suppressing false data latching caused by a rising edge on the STB signal. nSLEEP will remain HI until nORT is released (120 ms after DC-DC regulators come up).





nSLEEP = L (Bit 16 = L): Setup Mode Data Bit 0 Bit 1 S Bit 16 Bit 16 = LClock Strobe $t_{wi(clk)}$ $t_{wh(clk)}$ $t_{wh(clk)}$ t_{cs} t_{cs} $t_{wi(STRB)}$ $t_{wi(STRB)}$ t_{ss} t_{ss} min t_{ss} t_{ss} t_{ss} min t_{ss} t_{ss} min t_{ss} t_{ss} min t_{ss} t_{ss} t_{ss} min t_{ss} t_{ss} t_{ss} min t_{ss} t_{ss} t

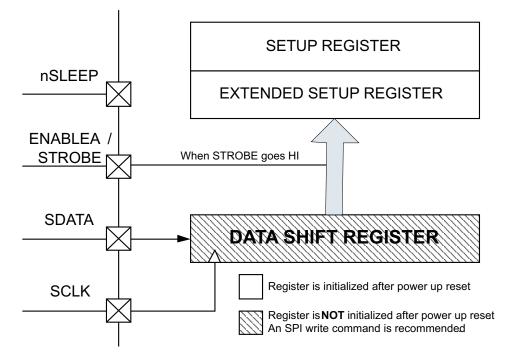
nSLEEP = L (Bit 16 = H): Extended Setup Mode



A. For initial setup, nSleep state can be "Don't care" before the tss_min timing prior to the strobe.

Figure 24. Serial Interface Timing





A. It is recommended that after initial power up sequence, a serial command be performed to clear undefined data in the internal shift register. This will help avoid latching undefined data into SETUP and EXTENDED SETUP registers. SETUP and EXTENDED SETUP registers are properly initialized during power up, but internal shift register is not initialized.

Figure 25. Serial Peripheral Interface Block Diagram

					 VI nPU (inter nOI	JC rnal)
				_	nSLEE ntil nORT is HI follows nSLEEP_e	
					nSLEE [interna	
					nSLEEP_int is LO	causes
848	Valid	Data		\$\$\$	Valid Data	Set Up regs
Undefined	i ///////		; ; ;		Valid Data hift Register data is ter a serial comma	Shift Regs valid and defined only

A. During startup (VM rising), internally nSLEEP de-asserted to HI, suppressing false data latching caused by a rising edge on the STB signal. nSLEEP will remain HI until nORT is released (120 ms after DC-DC regulators come up).

Figure 26. Serial Peripheral Interface STROBE Blocking During Power Up



8 Application and Implementation

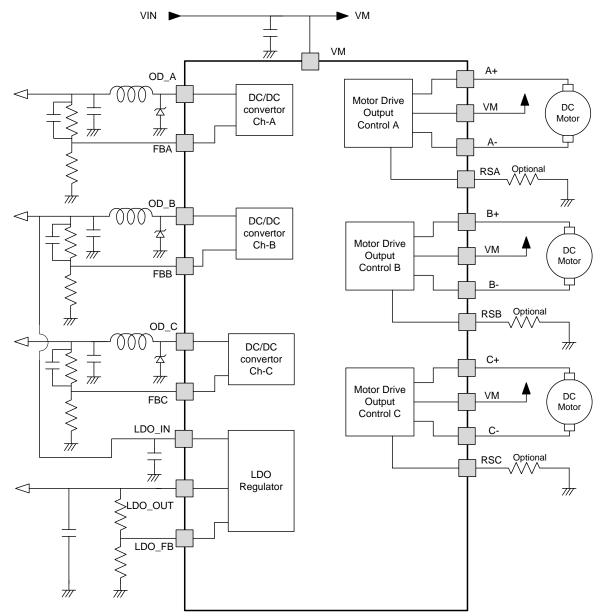
NOTE

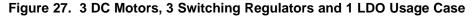
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The DRV8808 provides an integrated motor driver solution. The chip has three H-bridges internally and is configurable to different settings by SPI communication.

8.2 Typical Application







Typical Application (continued)

8.2.1 Design Requirements

To begin the design process, determine the following:

- Output voltage for each DC-DC converter and LDO.
- Output voltage start up sequence.
- Other parameters through SPI.

8.2.2 Detailed Design Procedure

8.2.2.1 Output Voltage for Each DC-DC Converter

Output voltage is set by external feedback resister network. For example,

1.5-V Output : 1.0 K Ω and 2.0 K Ω

1.0-V Output : 0 Ω and 3.0 K Ω

3.3-V Output : 6.8 K Ω and 1.5 K Ω

8.2.2.2 Output Voltage Start Up Sequence

DC-DC converters start up sequence is determined by CSELECT pin. See DC-DC Converters for details.

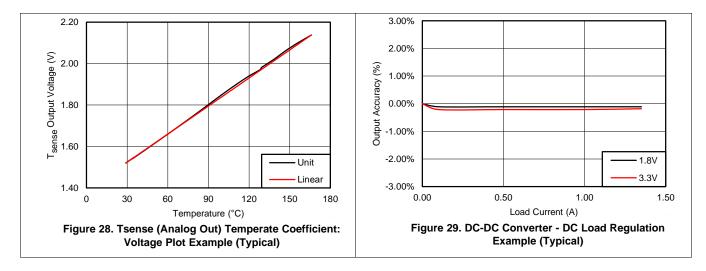
8.2.2.3 Other Parameters

Other parameters are programmed through SPI.

8.2.2.4 Motor Configuration

Many parameters are set by SPI register setting. Ramp up device with nSLEEP = Low, then write setup registers through SPI.

8.2.3 Application Curves





9 Power Supply Recommendations

This device requires a single voltage supply only. Supply to VM and LDOIN pins can be supplied by one of the switching regulator outputs.

10 Layout

10.1 Layout Guidelines

- Recommended to have GND plane layer for better thermal performance. Thermal pad directly going down to GND layer just under the device is the best way.
- Distance between Odx to Inductance should be as close as possible. This line has switching from 0 V to VM.
- FBx pin and external feedback resistor should be as close as possible. This is the analog sensing pin for the DC-DC converter.
- V3p3 pin is for internal analog reference voltage, and should be quiet. External 0.1 μF should be located closer.

10.2 Layout Example

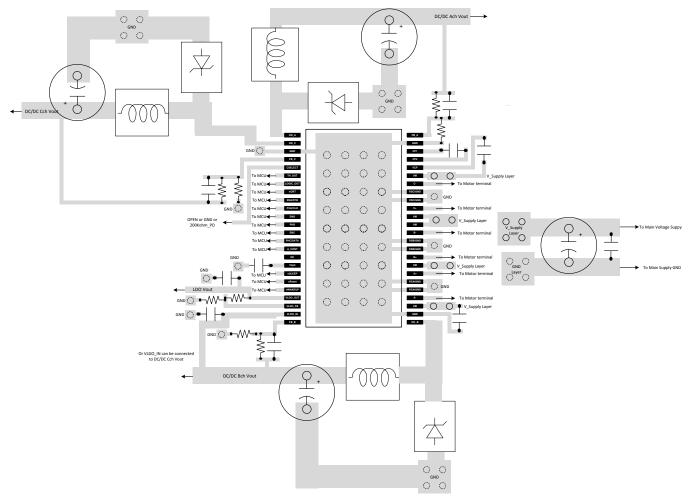


Figure 30. Layout Schematic



11 Device and Documentation Support

11.1 Trademarks

PowerPAD is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

11.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
DRV8808DCAR	NRND	HTSSOP	DCA	48	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	8808	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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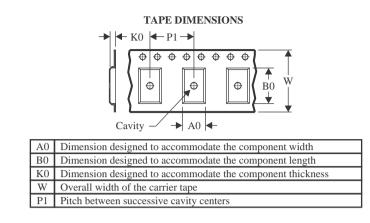


Texas

NSTRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8808DCAR	HTSSOP	DCA	48	2000	330.0	24.4	8.6	13.0	1.8	12.0	24.0	Q1



PACKAGE MATERIALS INFORMATION

5-Dec-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8808DCAR	HTSSOP	DCA	48	2000	350.0	350.0	43.0

DCA 48

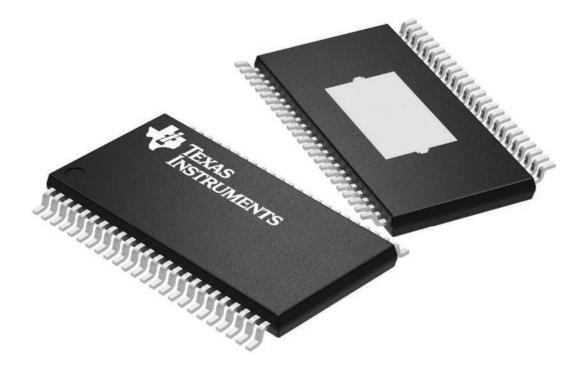
12.5 x 6.1, 0.5 mm pitch

GENERIC PACKAGE VIEW

HTSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

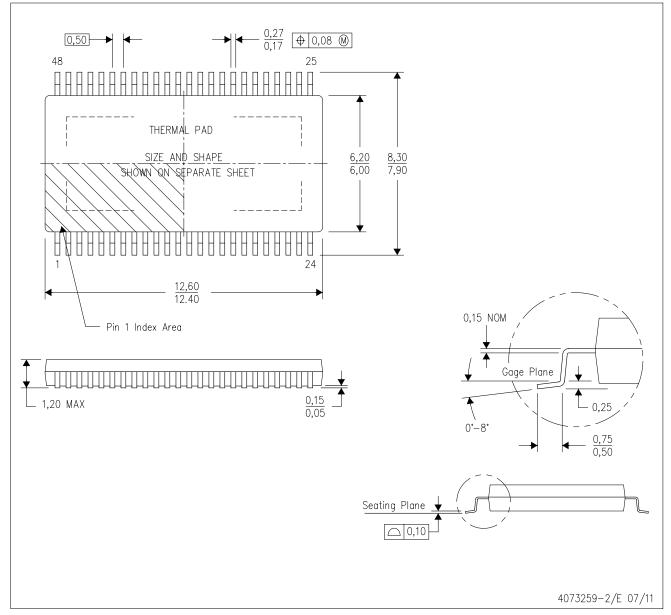
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





DCA (R-PDSO-G48)

PowerPAD[™] PLASTIC SMALL-OUTLINE



- NOTES: Α. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - Β. This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion not to exceed 0,15. C.
 - D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com.
 E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

 - F. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



DCA (R-PDSO-G48)

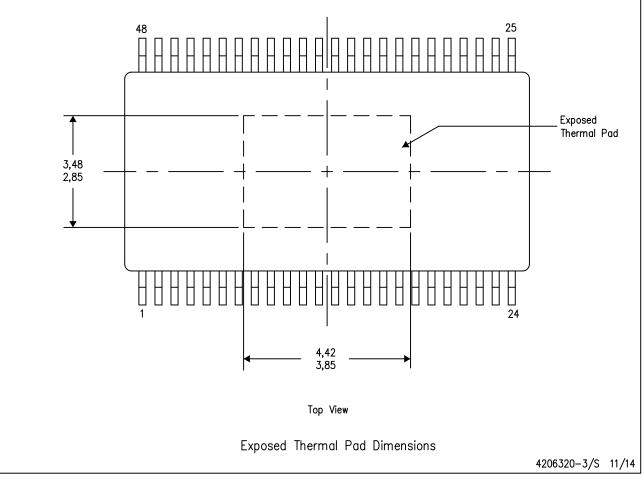
PowerPAD[™] PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD^{\mathbb{N}} package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



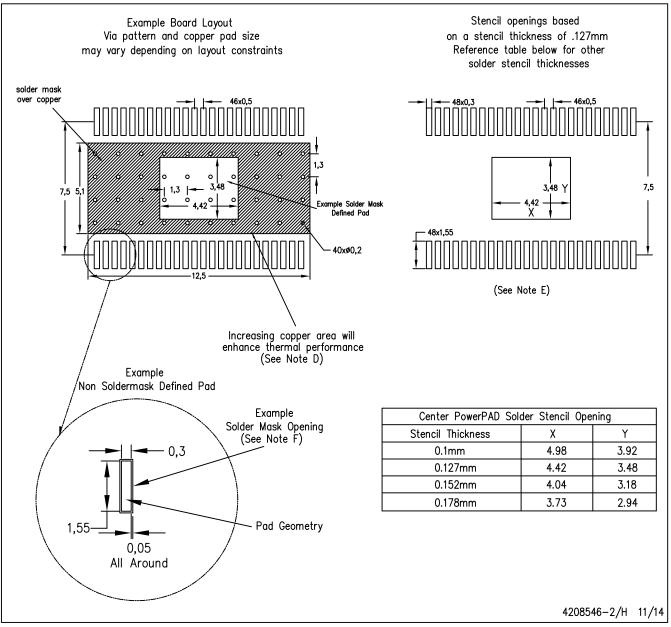
NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments.



DCA (R-PDSO-G48)

PowerPAD[™] PLASTIC SMALL OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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